Quad 2-Input NOR Gate

The MC74VHCT02A is an advanced high speed CMOS 2-input NOR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5 V CMOS level output swings.

The VHCT02A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

Features

- High Speed: $t_{PD} = 3.6 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 40 FETs or 10 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



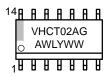
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT02ADR20	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT02ADTR20	TSSOP14 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

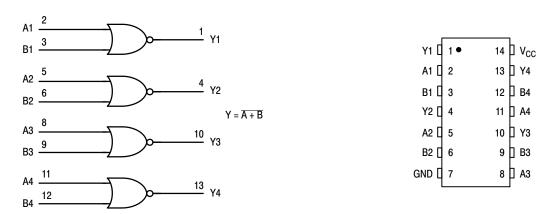


Figure 1. LOGIC DIAGRAM

Figure 2. PIN ASSIGNMENT

FUNCTION TABLE

Inp	Output	
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

MAXIMUM RATINGS

Symbol	Paramete	7	Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage		- 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current		± 20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and G	ND Pins	± 50	mA
P _D	Power Dissipation in Still Air,	SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{in}	DC Input Voltage		0	5.5	V
V _{out}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature		- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} =5.0V ±0.5V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	7	T _A = 25°(:	T _A ≤	85°C	T _A ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu \text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4\text{mA}$ $I_{OH} = -8\text{mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4\text{mA}$ $I_{OL} = 8\text{mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μА
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μА
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

			T _A = 25°C		$T_A \le 85^{\circ}C$ $T_A \le 125^{\circ}C$					
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Max	Max	Unit
t _{PLH} ,	Maximum Propagation Delay,	$V_{CC} = 3.0 \pm 0.3 V C_L = 15 pF$ $C_L = 50 pF$		5.6 8.1	7.9 11.4		9.5 13.0		12.5 17.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 V C_L = 15 pF$ $C_L = 50 pF$		3.6 5.1	5.5 7.5		6.5 8.5		9.0 11.0	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 1)	20	pF

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_{r} = t_{f} = 3.0 \text{ns}$, $C_{L} = 50 \text{pF}$, $V_{CC} = 5.0 \text{V}$)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

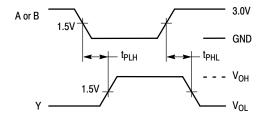
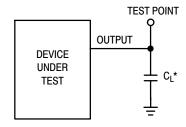


Figure 3. Switching Waveforms

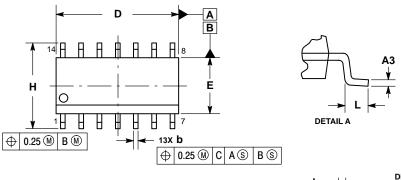


*Includes all probe and jig capacitance

Figure 4. Test Circuit

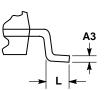
PACKAGE DIMENSIONS

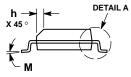
SOIC-14 CASE 751A-03 ISSUE K



C SEATING PLANE

е





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

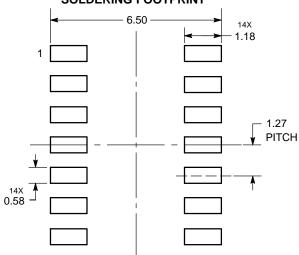
 3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
p	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
ø	1.27	BSC	0.050	BSC
Ŧ	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
м	0 °	7 °	0 °	7°

SOLDERING FOOTPRINT*

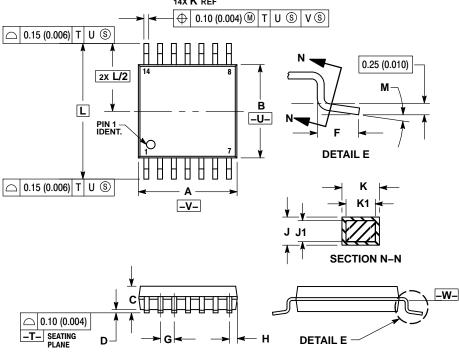


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 DT SUFFIX CASE 948G ISSUE B



NOTES:

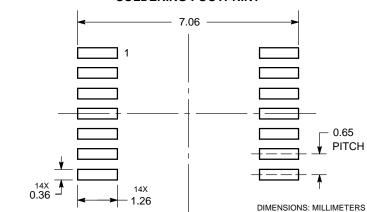
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- CONTROLLING DIMENSION. MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 LAGUE PAGE OF THE PROPRIES.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Г	6.40 BSC 0.252			BSC
М	0 °	8 °	0°	8 °

SOLDERING FOOTPRINT



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